4/2/12 Code: A-20

## Diplete - ET (NEW SCHEME) - Code: DE54

Max. Marks: 100

## Subject: ENGINEERING MATERIALS

Time: 3 Hours

## **DECEMBER 2009**

NOTE: There are 9 Questions in all.

- Question 1 is compulsory and carries 20 marks. Answer to Q.1 must be written in the space provided for it in the answer book supplied and nowhere else.
- Out of the remaining EIGHT Questions answer any FIVE Questions. Each question carries 16 marks.

Choose	e the correct or the best a	Iternative in the following:	(2×10)
a. A m	aterial which can store electr	etrical energy is	
	Capacitor	(B) Inductor	
<b>(C)</b>	Resistor	(D) Dielectric material.	
b. The	main purpose of a capacitor	is to	
(A)	block current flow	(B) help current flow	
<b>(C)</b>	store energy	(D) dissipate heat	
c. Mat	erials which provide path to	the magnetic flux are classified as	
(A)	insulating materials	(B) semiconducting materials	
<b>(C)</b>	magnetic materials	(D) dielectric materials	
d. A pı	ure semiconductor under ord	linary conditions behave like	
(A)	a conductor	(B) an insulator	
<b>(C)</b>	magnetic materials	(D) a ferroelectric material	
e. Whi	ch of the following materials	have maximum magnetic permeability?	
(A)	Pure iron	<b>(B)</b> 4% silicon steel	
(C)	Grain oriented Si-Fe	(D) Ni-Fe	
f. The	temperature at which a ferro	omagnetic material becomes a paramagnet	tic is called
(A)	Curie temperature	(B) Maximum temperature	
	Minimum temperature	(D) All the above	
g. In ph	oto emission of electrons the	e energies of electrons emitted depend on	the
(A)	intensity	(B) wavelength	
	velocity of light	(D) frequency	

h. The Fermi level is

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- Code: A-20 (A) an average value of all available energy levels **(B)** the highest occupied energy level at 0° K (C) an energy level at the top of the valence band (D) the largest available energy level In a p-n junction in equilibrium with zero bias (A) no holes or electrons cross the junction **(B)** only electrons cross the junction (C) equal number of electrons and holes cross the junction (**D**) only holes cross the junction The Hall voltage across an impurity semiconductor crystal can be increased by (A) increasing the concentration of impurity atoms in the crystal **(B)** increasing the thickness of the crystal (C) increasing the width of the crystal (D) increasing the current flowing through the crystal Answer any FIVE Questions out of EIGHT Questions. Each question carries 16 marks. a. Explain the effect of temperature on electrical conductivity of metals. (8)Q.2b. The resistivity of pure copper is 1.56 micro ohm cm. An alloy of copper containing one atomic percent of nickel has a resistivity of 2.81 micro ohm cm. An alloy of copper containing three atomic percent silver has a resistivity of 1.98 micro ohm cm. What is the resistivity of an alloy containing two atomic percent nickel and two atomic percent of silver? (8)(8)Q.3 a. Explain, the phenomenon of polarisation. b. Derive Clausius-Mossotti relation for dielectric constant  $\in_r$  and Polarisability  $\alpha$ . (8)**Q.4** Explain the dielectric properties of polymeric system. (8)Write a note on ferroelectricity and piezoelectricity. (8)Explain the phenomenon of Magnetostriction. Q.5 **(8)** Write a note on Silicon iron and Nickel iron alloy. (8)
  - b. Explain device potting, susceptor materials, reactors envelopes, plastic and pump fluids. **(8)**

**(8)** 

a. Explain zener breakdown and avalanche breakdown. (8)**Q.**7

a. Derive the relation between diffusion constant and mobility.

b. What are the different types of resistors? Explain metal oxide film resistors. **(8)** 

**Q.6** 

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Q.8	a.	a. Explain the two transistor analogue of an SCR.	
	b.	What are relays? Explain thermal type of relay.	(8)
Q.9	a.	Explain zone refining technique used for the purification of semiconductors.	(8)
	b.	Draw and explain the drain and transfer characteristics of JFET.	(8)